

In the Claims

1. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a first electrode electrically coupled to the thin film transistor;
a chemical vapor deposition insulating film having a low dielectric constant and a thickness of about 1 μm or more formed on the first electrode and the substrate, the chemical vapor deposition film having an opening portion for exposing the first electrode;
an organic electroluminescent layer forming a base and a sidewall in the opening portion;
and
a second electrode formed on the organic electroluminescent layer.
2. (Previously Presented) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film comprises SiOC.
3. (Previously Presented) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film has a dielectric constant less than about 3.5.
4. (Currently Amended) The device as claimed in claim 1, wherein the chemical vapor deposition insulating film is formed to have a thickness more than about 1 μm between the first electrode and the organic electroluminescent layer.
5. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate and having a gate insulating film, a gate electrode, and source/drain electrodes;
a passivation layer formed on the thin film transistor and the substrate;
a pixel electrode formed on the passivation layer so as to be connected with the thin film transistor;
a chemical vapor deposition insulating film having a low dielectric constant and a

thickness of about 1 μm or more formed on the pixel electrode and the passivation layer, the chemical vapor deposition insulating film having an opening portion for exposing the pixel electrode;

an organic electroluminescent layer forming a base and a sidewall in the opening portion;
and

a metal electrode formed on the organic electroluminescent layer and the chemical vapor deposition insulating film having a low dielectric constant.

6. (Previously Presented) The device as claimed in claim 5, wherein the chemical vapor deposition insulating film comprises SiOC.

7. (Previously Presented) The device as claimed in claim 5, wherein the chemical vapor deposition insulating film has a dielectric constant less than about 3.5.

8. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition insulating film has a thickness more than about 1 μm between the first electrode and the organic electroluminescent layer.

9. (Previously Presented) The device as claimed in claim 5, wherein the chemical vapor deposition insulating film and an edge portion of the pixel electrode overlap by more than about 1 μm .

10. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a stripe-shaped first electrode electrically coupled to the thin film transistor;
a chemical vapor deposition insulating film having a low dielectric constant and a thickness of about 1 μm or more formed on the first electrode and the substrate, the chemical vapor deposition insulating film having an opening portion formed on the first electrode with a tapered shape;
an organic electroluminescent layer forming a base and a sidewall in the opening portion;

and

a stripe-shaped second electrode formed on the organic electroluminescent layer, the stripe-shaped second electrode being arranged to cross the first electrode.

11. (Previously Presented) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film is comprised of SiOC.

12. (Previously Presented) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film has a dielectric constant less than about 3.5.

13. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition insulating film has a thickness more than about 1 μm between the first electrode and the organic electroluminescent layer.